

QSiC™ 1200V SiC MOSFET

V_{DS}	1200 V
$R_{DS,on}$	77 mΩ
I_D (TC=25°C)	35 A
$T_{J,max}$	175°C

Features

- High speed switching
- Reliable body diode
- All parts tested to above 1400V
- Avalanche tested to 200mJ

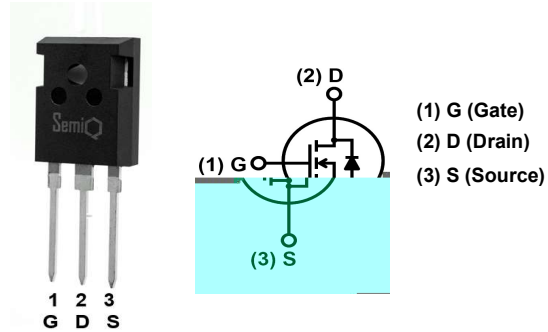
Benefits

- Lower capacitance
- Higher system efficiency
- Easy to parallel

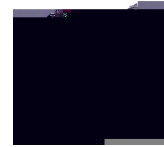
Applications

- Solar Inverters
- Switch mode power supplies, UPS
- Induction Heating and Welding
- EV charging stations
- High Voltage DC/DC Converters
- Motor Drives

Package



Part #	Package	Marking
GP2T080A120U	TO-247-3L	2T080A120U



Maximum Ratings, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit
Drain-Source Voltage	V_{rated}	$V_{GS}=0V$, $I_D=1\mu A$	1200	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$, $V_{GS}=20V$	35	A
		$T_C=100^\circ\text{C}$, $V_{GS}=20V$	26	
Pulsed Drain Current	$I_{D,pulse}$	$T_C=25^\circ\text{C}$	80	
Gate Source Voltage	V_{GSmax}		-10/25	V
	V_{GSop}	Recommended operational	-5/20	
Power Dissipation	P_{tot}	$T_C=25^\circ\text{C}$	188	W
Operating & Storage Temperature	T_J , $T_{storage}$	Continuous	-55...175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=1mH$, $I_{AS}=20.0A$, $V=50V$	200	mJ

Thermal Characteristics

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal Resistance, Junction to Case	R_{thJC}		-	0.65	0.80	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	R_{thJA}		-	-	40.0	

Static Electrical Characteristics, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=1mA$	1200	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=1200V, V_{GS}=0V$	-	0.1	1.0	μA
		$V_{DS}=1200V, V_{GS}=0V, T_J=175^\circ\text{C}$	-	1	-	
Gate-Source Leakage Current	I_{GSS+}	$V_{GS}=20V, V_{DS}=0V$	-	10	100	nA
	I_{GSS-}	$V_{GS}=-5V, V_{DS}=0V$	-	-10	-100	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=10mA$	1.8	2.8	4	V
		$V_{GS}=V_{DS}, I_D=10mA, T_J=125^\circ\text{C}$	-	2.1	-	
		$V_{GS}=V_{DS}, I_D=10mA, T_J=175^\circ\text{C}$	-	1.9	-	
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=20V, I_D=20A$	-	77	100	m Ω
		$V_{GS}=20V, I_D=10A$	-	71	90	
		$V_{GS}=20V, I_D=20A, T_J=125^\circ\text{C}$	-	106	-	
		$V_{GS}=20V, I_D=20A, T_J=175^\circ\text{C}$	-	134	-	
Gate Input Resistance	R_G	$f=1MHz, V_{AC}=25mV, D-S \text{ Short}$	-	3.0	-	Ω

AC Electrical Characteristics, at $T_J=25^\circ\text{C}$, unless otherwise specified

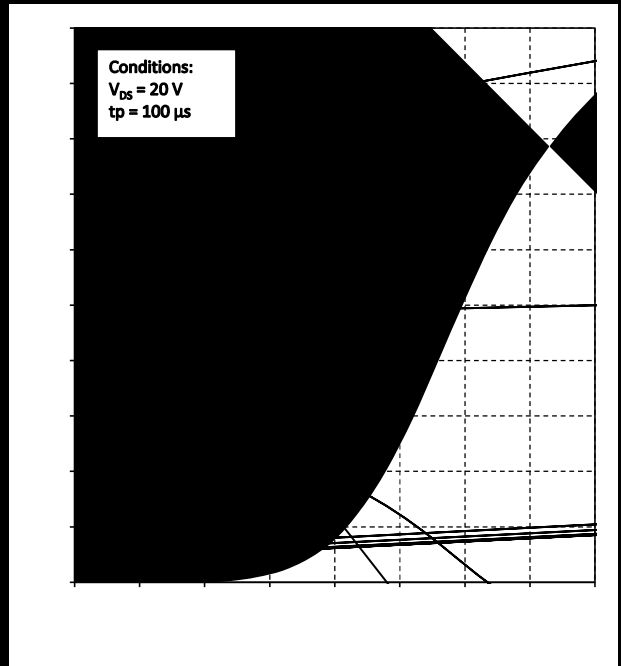
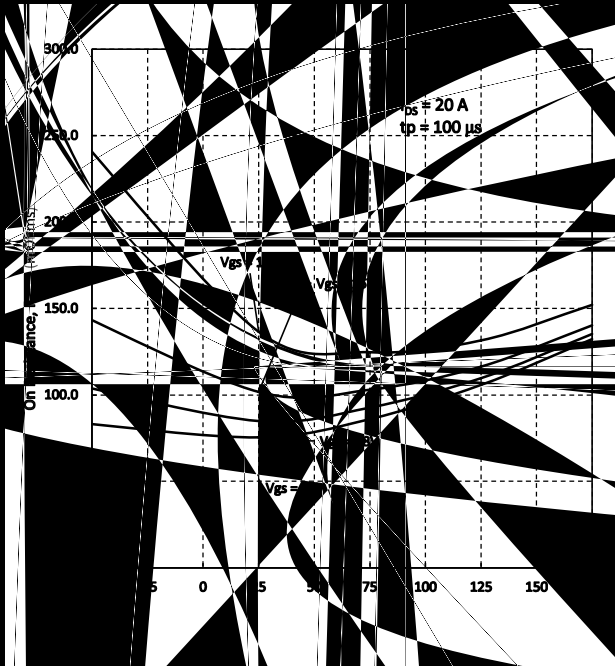
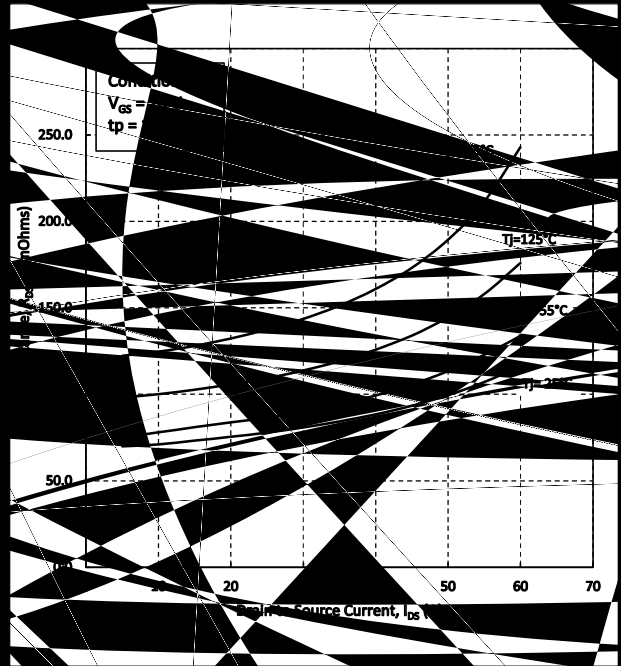
Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Input Capacitance	C_{ISS}	$V_{GS}=0V$ $V_{DS}=1000V$ $f=200kHz, V_{AC}=25mV$	-	1377	-	pF
Output Capacitance	C_{OSS}		-	62	-	
Reverse Transfer Capacitance	C_{RSS}		-	4	-	
Coss Stored Energy	E_{OSS}		-	38	-	
Turn-On Switching Energy	E_{ON}	$V_{DD}=800V, I_{DS}=20A,$ $R_{G(ext)}=2.5\Omega,$ $V_{GS}=-5/+20V, L=975\mu H,$ FWD = GP2T080A120U	-	410	-	μJ
Turn-Off Switching Energy	E_{OFF}		-	22	-	
Total Switching Energy	E_{TOT}		-	432	-	
Turn-On Switching Energy	E_{ON}	$V_{DD}=800V, I_{DS}=20A,$ $R_{G(ext)}=2.5\Omega,$ $V_{GS}=-5/+20V, L=975\mu H,$ FWD = GP3D010A120A	-	339	-	μJ
Turn-Off Switching Energy	E_{OFF}		-	23	-	
Total Switching Energy	E_{TOT}		-	362	-	
Turn-On Delay Time	$t_{D(on)}$	$V_{DD}=800V, I_{DS}=20A,$ $R_{G(ext)}=2.5\Omega, V_{GS}=-5V/20V,$ $L=975\mu H,$ FWD = GP2T080A120U	-	10	-	ns
Rise Time	t_R		-	6	-	
Turn-Off Delay Time	$t_{D(off)}$		-	16	-	
Fall Time	t_F		-	10	-	
Total Gate Charge	Q_G	$V_{DD}=800V, I_{DS}=20A$ $V_{GS}=-5/20V$	-	58	-	nC
Gate to Source Charge	Q_{GS}		-	18	-	
Gate to Drain Charge	Q_{GD}		-	17	-	

Body Diode Characteristics, at $T_J=25^\circ\text{C}$, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Max Continuous Diode Fwd Current	I_S	$V_{GS}=-5V, T_C=25^\circ\text{C}$	-	-	43	A
Diode Forward Voltage	V_{SD}	$V_{GS}=-5V, I_S=10A$	-	3.8	-	V
Reverse Recovery Time	t_{RR}	$I_S=20A, V_R=800V, V_{GS}=-5V$ $di_F/dt=3500A/us$	-	26	-	ns
Reverse Recovery Charge	Q_{RR}		-	124	-	nC
Peak Reverse Recovery Current	I_{RRM}		-	8	-	A

Conditions:
 $V_{GS} = 20$
 $t_p = 100 \mu s$

Realize $R_{DS(ON)} = 20 \Omega$ @ $25^\circ C$



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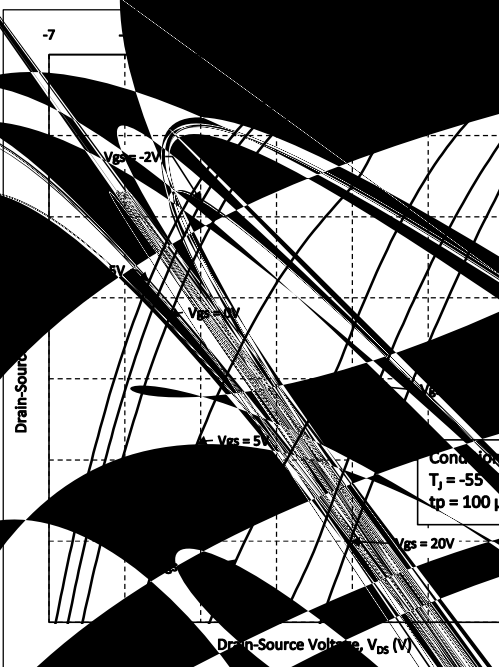


Figure 9. Body Diode Characteristics at $T_J = -55^\circ\text{C}$

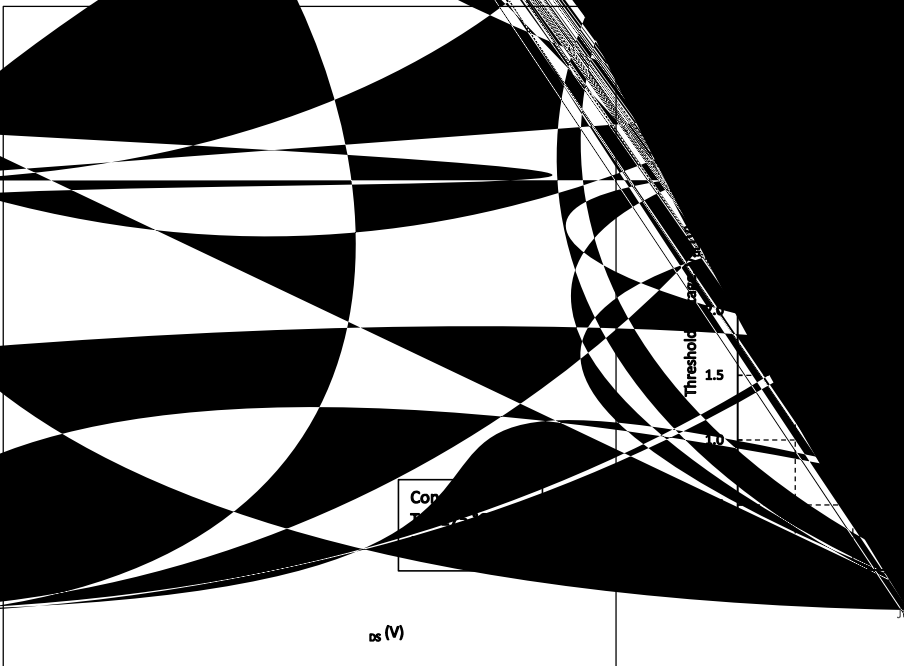


Figure 11. Body Diode Characteristics at $T_J = 175^\circ\text{C}$

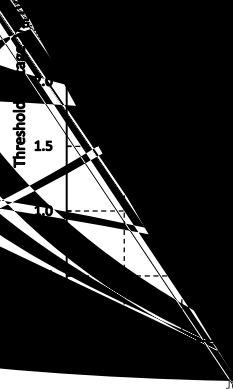


Figure 12. Threshold Voltage

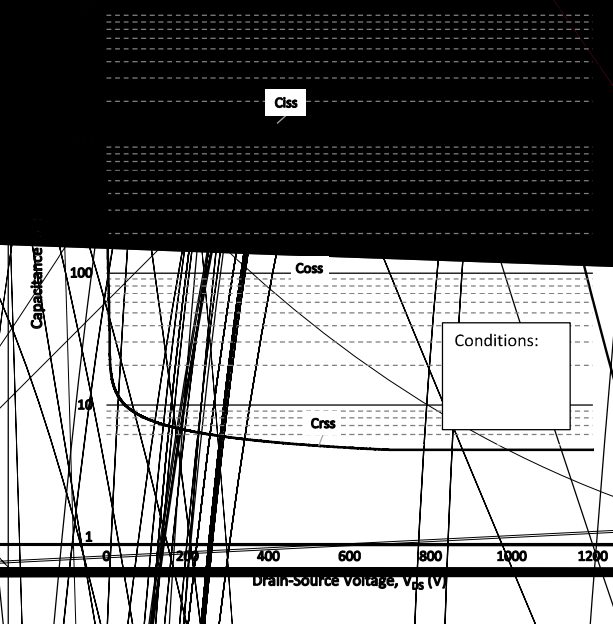


Figure 15. Capacitance vs Drain-Source Voltage

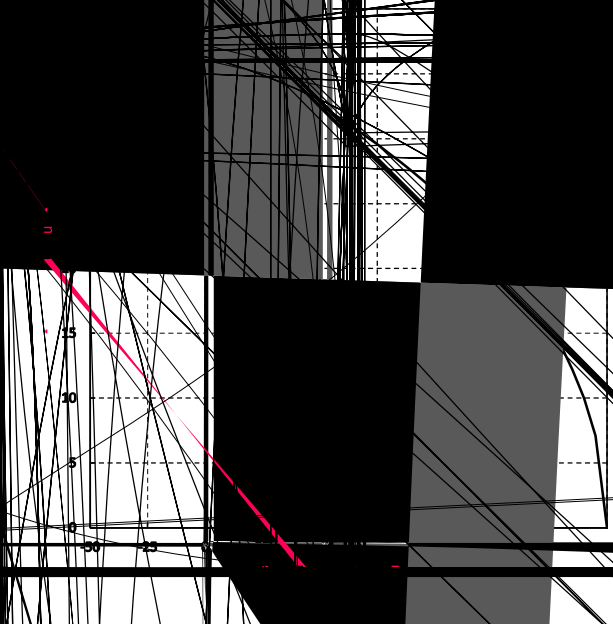
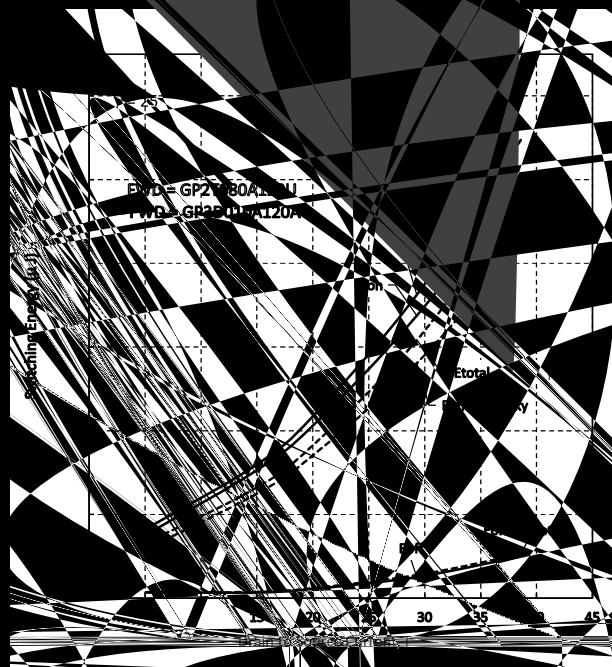
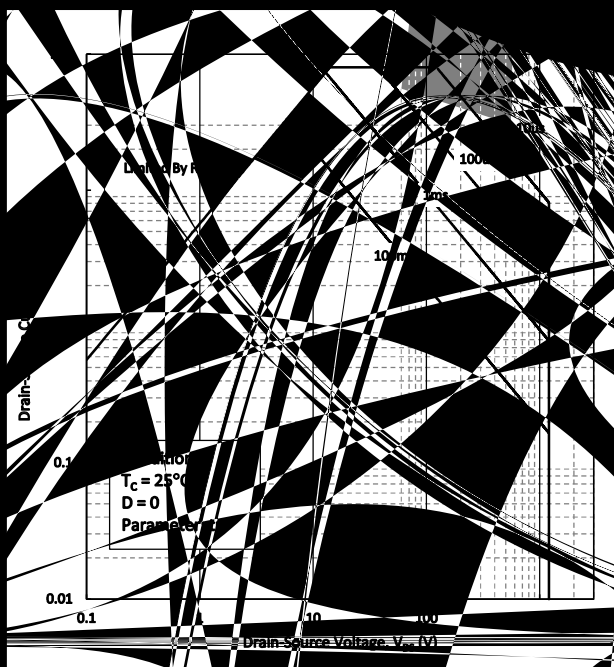


Figure 16. Continuous Drain Current vs. Case Temperature



MOSFET

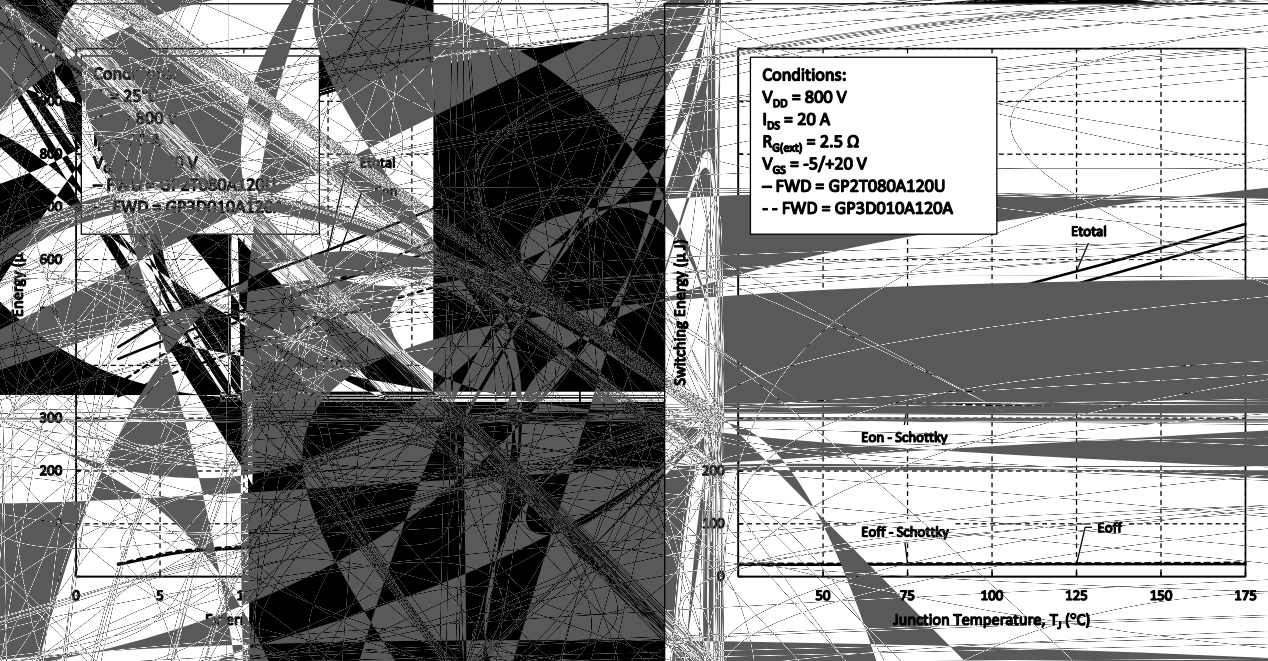
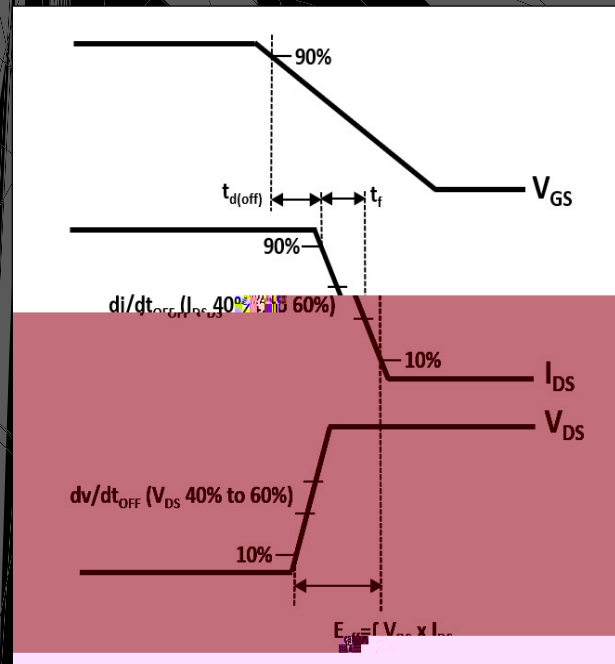
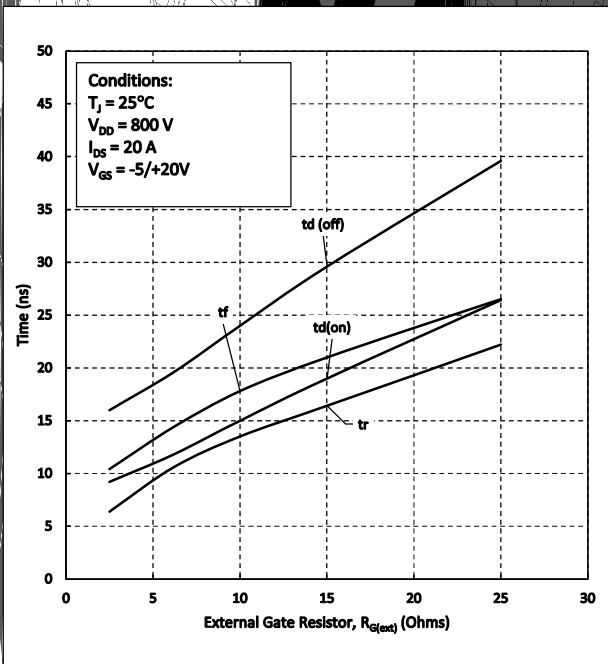


Figure 21. Clamped Inductor



23. Switch

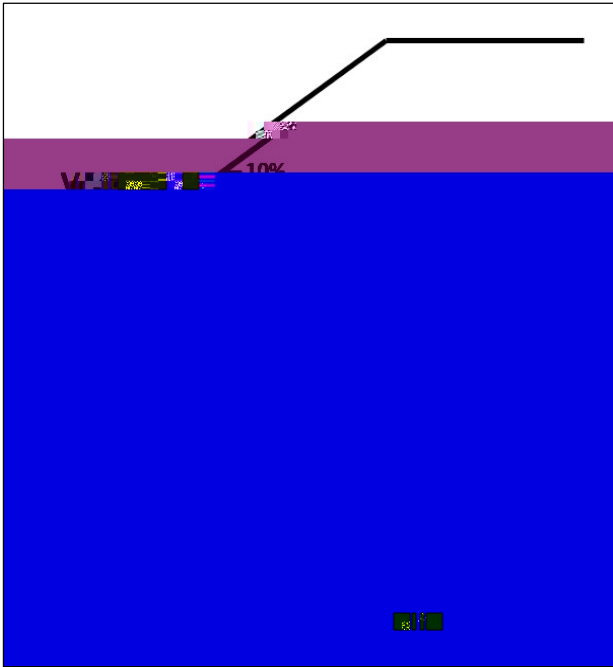


Figure 25. Turn-on Transient Definitions

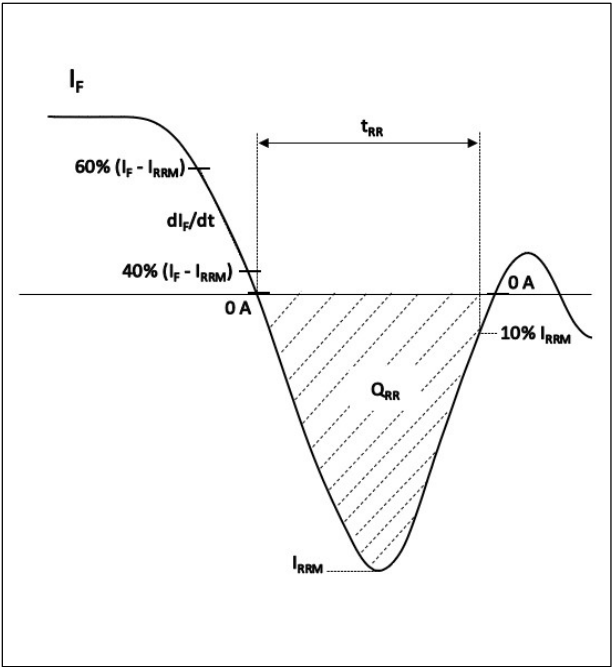
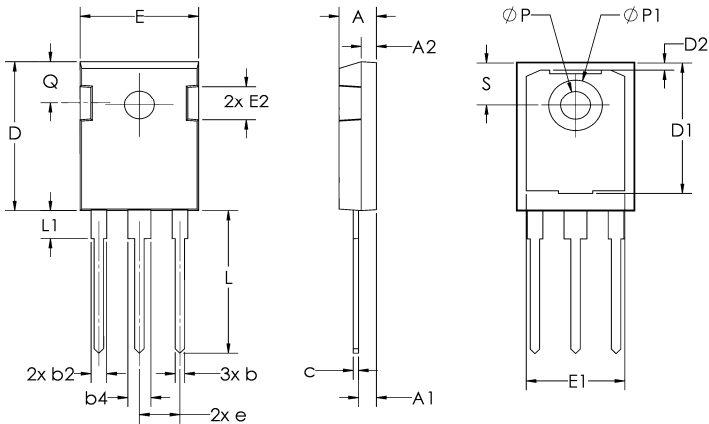


Figure 26. Reverse Recovery Definitions

Package Dimensions TO-247-3L



Sym	Millimeters		Inches	
	Min	Max	Min	Max
A	4.70	5.31	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.80	21.46	0.819	0.845
D1	13.08	17.65	0.515	0.695
D2	0.51	1.35	0.020	0.053
E	15.49	16.26	0.610	0.640
E1	13.46	14.16	0.530	0.557
E2	3.43	5.49	0.135	0.216
e	5.44 BSC		0.214 BSC	
L	19.81	20.32	0.780	0.800
L1	4.10	4.50	0.161	0.177
ØP	3.56	3.66	0.140	0.144
ØP1	7.06	7.39	0.278	0.291
Q	5.39	6.20	0.212	0.244
S	6.04	6.30	0.238	0.248

Notes**RoHS Compliance**

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

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REACH substances of high concern (SVHC) information is available for this product. Since the European Chemicals Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at SemiQ Headquarters in Lake Forest, California to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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